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(12) **UK Patent Application** (19) **GB** (11) **2 189 166** (13) **A**

(43) Application published 21 Oct 1987

(21) Application No 8609480

(22) Date of filing 18 Apr 1986

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C30B 15/04 C01G 15/00 28/00

(52) Domestic classification (Edition I):

B1S 121 122 129 BDAB BDN10

C1A 421 4 E6G E9 G55 G56 G5 N55 N56 N5 PF9A VG2

U1S 1421 B1S C1A

(56) Documents cited

GB 1183247

(58) Field of search

B1S

C1A

Selected US specifications from IPC sub-classes C30B

C01B C01G

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(54) A single crystal of IIIb-Vb compound, particularly GaAs, and method for producing the same

(57) A single crystal of IIIb-Vb group compound contains  $1 \times 10^{17} \sim 8 \times 10^{19} \text{ cm}^{-3}$  of oxygen and has a dislocation density which is low and uniform in a direction perpendicular to the growth direction.

An LEC method for crystal growth of a single crystal of GaAs comprises an addition of oxide at an oxygen concentration of  $1 \times 10^{17} \sim 2 \times 10^{21} \text{ cm}^{-3}$ .

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## SPECIFICATION

A single crystal of IIIb-Vb compound, particularly GaAs, and method for producing the same

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## BACKGROUND OF THE INVENTION

## 1. Field of the Invention

The present invention relates to a IIIb-Vb group compound single crystal (hereinafter referred to as "IIIb-Vb single crystal"), particularly to a gallium arsenide (GaAs) single crystal having a low dislocation density, and a production method thereof, in particular, to a liquid encapsulated Czocharlski method (hereinafter referred to as the "LEC method"). The single crystal GaAs has a high electron mobility and hence is widely used for an UHF or SHF element, a high-speed switching element, and a substrate of integrated circuit (IC) ("Information Processing" 25 (1) pp 37-46 (1984) by Hideki Hasegawa).

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## 2. Description of the Related Arts

The properties required of a IIIb-Vb single crystal, such as GaAs, when used as the above electronic elements and IC substrate, are a high level of purity, a high degree of crystalline perfection, and uniform electrical properties. A semi-insulative property is necessary for the IC substrate.

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Dislocation, which degrades the crystalline perfection, causes malfunctions in ICs. Thus, in order to use the IIIb-Vb single crystal for a substrate of highly integrated ICs and high output FETs having a large chip area, a IIIb-Vb single crystal having a low dislocation density is first produced and then cut into wafers. The LEC method is used for producing a GaAs single crystal for use as the substrate of an IC or the like, since the thus-produced GaAs has a large diameter and a high level of purity needed to enhance the activation rate of ions implanted in a GaAs substrate (BULLETIN OF THE JAPAN INSTITUTE OF METALS. Vol 23 (1984), No. 7, pp 586~592).

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In the LEC method, the  $B_2O_3$  melt, which is an encapsulant, covers the surface of the melt of IIIb-Vb group compound. The temperature gradient across the layer of the  $B_2O_3$  melt can amount to  $100^\circ\text{C}/\text{cm}$ , and hence is considered high as compared with the horizontal boat growth method. The GaAs single crystal pulled from the GaAs melt undergoes great thermal stress during passage through the layer of the  $B_2O_3$  melt. This thermal stress is one cause of the generation of a number of dislocations in the IIIb-Vb single crystal. The dislocation density, in terms of etch pit density (EPD) of the GaAs single crystals produced by the LEC method, generally ranges from approximately  $10^4$  to  $10^5 \text{ cm}^{-2}$ . The dislocation distribution of GaAs single crystals produced by the LEC method, in a plane perpendicular to the pulling-up direction, is such that it is highest around the periphery, and is at its next highest level in the center of the IIIb-Vb single crystals. The dislocation density, therefore, may be seen as a W shape, in which a low dislocation-density region is formed around the center and is encompassed by the outer, highest dislocation-density regions.

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B. Jacob describes in "Semi-Insulating III-V Materials" S. Makram-Ebid et al. Ed. p. 2~18 (1984) Shiva Publishing Ltd., a method for decreasing the dislocation by adding indium, which is an electrically neutral impurity, to the GaAs. According to this method, a GaAs single crystal is pulled up from the melt, to which metallic indium has been added in an amount of from  $10^{18}$  to  $10^{20} \text{ cm}^{-3}$ , and the dislocation density is drastically decreased by this In addition.

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The present inventors investigated the dislocation density of IIIb-Vb single crystals produced by the LEC method, and found a drastic reduction occurred in EPD of (100). Nevertheless, in several GaAs single crystals, etch pits arranged linearly in the  $\langle 110 \rangle$  direction around the periphery were discovered, and EPD occasionally exceeded  $1 \times 10^4 \text{ cm}^{-2}$  in the region containing the etch pits.

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## SUMMARY OF THE INVENTION

It is an object of the present invention to provide a IIIb-Vb single crystal which is free of locally high EPD and thus has a low EPD through the crystal.

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It is another object of the present invention to improve an LEC method for the growth of a IIIb-Vb group compound, thereby preventing locally high EPD in a plane perpendicular to the pulling direction.

## 60 DESCRIPTION OF THE PREFERRED EMBODIMENTS

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*IIIb-Vb Single Crystal*

The IIIb-Vb single crystal according to the present invention is characterized by containing from  $1 \times 10^{17}$  to  $8 \times 10^{19} \text{ cm}^{-3}$  of oxygen.

When the oxygen concentration of the IIIb-Vb single crystal is less than  $1 \times 10^{17} \text{ cm}^{-3}$ , the amount of linear etch pits becomes appreciable, and thus the phenomenon of locally high EPD

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cannot be prevented. On the other hand, when the oxygen concentration exceeds  $8 \times 10^{19} \text{ cm}^{-3}$ , the crystalline properties are degraded. The compounds of IIIb-Vb group are GaAs, InAs and InP.

The In concentration of the IIIb-Vb single crystal is preferably from  $1 \times 10^{18}$  to  $1 \times 10^{20} \text{ cm}^{-3}$ .

At the In concentration less than  $1 \times 10^{18} \text{ cm}^{-3}$ , the EPD tends to increase. On the other hand, when the In concentration of the GaAs single crystal exceeds  $1 \times 10^{20} \text{ cm}^{-3}$ , the IIIb-Vb single crystal tends to embrittle and disadvantageous precipitation and the like of In tends to occur. A more preferred In concentration is from  $2 \times 10^{19}$  to  $5 \times 10^{19} \text{ cm}^{-3}$ .

#### *GaAs Single Crystal Containing Oxygen and Indium*

This GaAs single crystal can be produced by growing GaAs from a GaAs melt, to which from  $1 \times 10^{19}$  to  $1 \times 10^{21} \text{ cm}^{-3}$  of In and from  $1 \times 10^{18}$  to  $2 \times 10^{21} \text{ cm}^{-3}$  of oxygen are added. The preferred added concentrations of In and oxygen are from  $2 \times 10^{20}$  to  $5 \times 10^{21} \text{ cm}^{-3}$ , and from  $1 \times 10^{18}$  to  $3 \times 10^{19} \text{ cm}^{-3}$ , respectively. The addition concentration herein indicates the number of atoms of In or oxygen added to  $1 \text{ cm}^3$  of the melt. When the addition concentrations lie outside the ranges mentioned above, the preferred In concentration and requisite oxygen concentration cannot be ensured in the GaAs single crystal.

The addition of In and oxygen to the GaAs melt is preferably carried out by using indium oxide ( $\text{In}_2\text{O}_3$ ). In this case, the indium oxide is added to obtain an In concentration of from  $1 \times 10^{19}$  to  $1 \times 10^{21} \text{ cm}^{-3}$  in the GaAs melt. Alternatively, In and oxygen may be separately added. In this case, In in the metallic form, and oxygen in the form of As (III) oxide ( $\text{As}_2\text{O}_3$ ) and gallium oxide ( $\text{Ga}_2\text{O}_3$ ) are added to the melt to obtain the requisite concentrations in the melt.

The crystal growth method used for growing the GaAs single crystal from the melt, to which In and oxygen are added, is preferably the LEC method using an encapsulant, such as  $\text{B}_2\text{O}_3$  or the like, since a high oxygen concentration in the melt can be thus attained, contamination of the melt by a crucible and an encapsulant is slight, and productivity is high. This crystal growth method could be used in a boat growth method, such as a gradient freeze method or horizontal Bridgman method.

During the crystal growth, impurities, such as Si, S, Cr, and the like, which determine the electrical properties, may or may not be added to the melt. The undoped, semi-insulative GaAs single crystal which does not contain the impurities at all, is appropriate as a substrate for UHF or SHF elements and ICs.

The crystal growth direction is preferably in the  $\langle 100 \rangle$  direction, since a round substrate is thus obtained. The crystal growth direction, however, may be  $\langle 111 \rangle$ .

#### *LEC Method for Growing Single Crystal of IIIb-Vb Compound*

The LEC method for growing a IIIb-Vb single crystal using an encapsulant, according to the present invention, is characterized by adding at least one oxide selected from the group consisting of oxide of the IIIb-group element and oxide of the Vb group element to the melt of the IIIb-Vb group compound at an oxygen concentration of at least one oxide of from  $1 \times 10^{18}$  to  $2 \times 10^{21}$ , preferably from  $1 \times 10^{19}$  to  $1 \times 10^{21}$  per  $\text{cm}^3$  of the melt of the IIIb-Vb group compound.

When the IIIb-Vb group compound is GaAs, the oxide of the IIIb element is preferably gallium oxide ( $\text{Ga}_2\text{O}_3$ ) and the oxide of the Vb element is preferably diarsenic trioxide.

When the IIIb-Vb group compound is GaP, the oxide is preferably  $\text{Ga}_2\text{O}_3$ .

When the IIIb-Vb group compound is InP, the oxide is preferably  $\text{In}_2\text{O}_3$ .

When the IIIb-Vb group compound is InAs, the oxide of the IIIb element is preferably  $\text{In}_2\text{O}_3$  and the oxide of the Vb element is preferably  $\text{As}_2\text{O}_3$ .

A special LEC growth device is not required for carrying out the method according to the present invention, and a usual such device may be used. A preferable crucible is made of PBN (pyrolytic boron nitride) or is coated with PBN, since the contamination of the melt by the crucible is slight. Graphite is less preferable but may be used as the material of a crucible or vessel.

The heating is usually carried out by means of a graphite resistance-heater having a cylindrical or wine-glass shape. The temperature gradient in the LEC growth device may be adjusted, if necessary, by disposing a heat-shield made of graphite or a cylindrical heater above the crucible or vessel. The interior of LEC growth apparatus is pressurized, during the crystal growth, to a pressure of usually from 10 to 60  $\text{kg/cm}^2$  (gauge pressure) by using an inert gas, such as argon or nitrogen. As the liquid sealant, high purity boron oxide ( $\text{B}_2\text{O}_3$ ) thoroughly desiccated is ordinarily used.

When commencing the growth of a IIIb-Vb single crystal, a predetermined amount of  $\text{B}_2\text{O}_3$  and polycrystalline IIIb-Vb compound are loaded in a crucible or the like. However, instead of loading the IIIb-Vb compound, a metallic IIIb element and elementary Vb in an amount slightly greater than the stoichiometric amount may be loaded. In this case, the IIIb-V melt is formed during heating and temperature-elevating the crucible or the like.

Subsequently, at least one of the oxide of the IIIb group element, e.g., gallium oxide ( $\text{Ga}_2\text{O}_3$ ), and the oxide of the Vb group element, e.g., diarsenic trioxide ( $\text{As}_2\text{O}_3$ ), is loaded into the

crucible or the like. The addition amount of  $\text{Ga}_2\text{O}_3$  and/or  $\text{As}_2\text{O}_3$  is not the analysis value but the calculation value, namely such that the number of oxygen atoms of  $\text{Ga}_2\text{O}_3$  and/or  $\text{As}_2\text{O}_3$  added amounts to a concentration of from  $1 \times 10^{18}$  to  $2 \times 10^{21}$ , preferably  $3 \times 10^{18}$  to  $3.5 \times 10^{20}$ , per  $\text{cm}^3$  of the melt. When the oxygen concentration is less than  $1 \times 10^{18} \text{ cm}^{-3}$ , it is difficult to decrease the dislocation density of the obtained IIIb-Vb single crystal. On the other hand, when the oxygen concentration exceeds  $2 \times 10^{21} \text{ cm}^{-3}$ , a IIIb-Vb single crystal is difficult to obtain, and even if a IIIb-Vb single crystal is obtained, crystal defects, such as dislocations, are disadvantageously increased.

$\text{Ga}_2\text{O}_3$  and  $\text{As}_2\text{O}_3$  may be added alone or together at an optional proportion to one another.

10 An equal molar ratio of  $\text{Ga}_2\text{O}_3$  and  $\text{As}_2\text{O}_3$  is preferred, because this suppresses the generation of vacancies.

The conditions for LEC growth other than those described above are the same as usual.

15 The IIIb-Vb single crystal produced by the method according to the present invention has a dislocation density, in terms of EPD, lower than that obtained by conventional methods, and attains an EPD of  $5000 \text{ cm}^{-2}$  or less. In the IIIb-Vb single crystal produced by the method according to the present invention, the distribution of dislocations in a plane perpendicular to the pulling direction is uniform.

The present invention is further explained with reference to the examples and comparative examples.

20 In the examples and comparative examples, the LEC crystal puller used was an "MSR-6" type manufactured by the Cambridge Instruments Co., Ltd. of Britain.

EPD was measured by dipping test samples in fused potassium hydroxide at  $350^\circ\text{C}$  for 20 minutes and then counting the amount of etch pits, under a microscope.

25 The oxygen concentration of wafers was measured by using a secondary-ion mass analysis device "CAMECA 3F" type manufactured by the Thomson CFS Co., Ltd. of France.

The In concentration of the wafers was measured by using an atomic absorption analyzer "AAS-4000" type produced by the "Perkinson-Elmer" Co., Ltd. of the U.S.A.

#### Example 1

30 500 g of Ga, 550 g of As, 4.5 g of  $\text{In}_2\text{O}_3$  (corresponding to the In addition concentration of  $1 \times 10^{20} \text{ cm}^{-3}$  and the oxygen addition concentration of  $1.5 \times 10^{20} \text{ cm}^{-3}$ ) and 150 g of  $\text{B}_2\text{O}_3$  were contained in a crucible made of PBN (pyrolytic boron nitride) and having an inner diameter of 100 mm. The interior of the LEC crystal puller was pressurized to  $65 \text{ kg/cm}^2$  (gauge pressure) and the crucible was heated to  $1400^\circ\text{C}$  to form the GaAs melt. The crucible temperature was then lowered to  $1350^\circ\text{C}$ . While the crucible and a seed crystal were rotated, the seed crystal was brought into contact with the GaAs melt and then pulled upwards to attain a growth of a GaAs single crystal in the  $\langle 100 \rangle$  direction. The obtained GaAs single crystal has a weight of 650 g and diameter of 50 mm. A (100) wafer was cut from the top end of a straight body portion of the single crystal and subjected to the EPD measurement. The EPD of the wafer, except for a 6 mm wide outer peripheral part, was  $900 \text{ cm}^{-2}$  in average and  $1100 \text{ cm}^{-2}$  at greatest. No linearly arranged etch pits were detected.

The In concentration of the wafer was  $9.5 \times 10^{18} \text{ cm}^{-3}$  and the oxygen concentration of the wafer was  $8 \times 10^{17} \text{ cm}^{-3}$ .

#### 45 Example 2

The procedure of Example 1 was repeated to produce the GaAs single crystal, except that instead of  $\text{In}_2\text{O}_3$  added in the case of Example 1, 1.89 g of metallic In and 3.2 g of  $\text{As}_2\text{O}_3$  (the In addition concentration was  $5 \times 10^{19}$  and the oxygen addition concentration was  $1.5 \times 10^{20}$  relative to  $\text{cm}^3$  of the GaAs melt) were added.

50 A (100) wafer was cut from the top end of a straight body portion of the single crystal and subjected to the EPD measurement. The EPD of the wafer, except for a 6 mm wide outer peripheral part, was  $1200 \text{ cm}^{-2}$  in average and  $1500 \text{ cm}^{-2}$  at greatest. No linearly arranged etch pits were detected.

55 The In concentration of the wafer was  $5 \times 10^{18} \text{ cm}^{-3}$  and the oxygen concentration of the wafer was  $6 \times 10^{17} \text{ cm}^{-3}$ .

#### Comparative Example 1

60 The procedure of Example 1 was repeated to produce the GaAs single crystal, except that instead of the  $\text{In}_2\text{O}_3$  added in the case of Example 1, 3.7 g of metallic In (the In addition concentration was  $9.95 \times 10^{19}$  relative to  $\text{cm}^3$  of the GaAs melt) was added.

A (100) wafer was cut from the top end of a straight body portion of the single crystal and subjected to the EPD measurement. The EPD of the wafer, except for a 6 mm wide outer peripheral part, was  $1000 \text{ cm}^{-2}$  in average and  $5000 \text{ cm}^{-2}$  at greatest. Linearly arranged etch pits were detected at portions of the wafer where the EPD was greater than  $1000 \text{ cm}^{-2}$ .

65 The In concentration of the wafer was  $1 \times 10^{18} \text{ cm}^{-3}$  and the oxygen concentration of the

wafer was  $2 \times 10^{16} \text{ cm}^{-3}$ .

### Example 3

1500 g of Ga, 1631.6 g of As, 1.5 g of  $\text{Ga}_2\text{O}_3$ , 1.58 g of  $\text{As}_2\text{O}_3$ , and 600 g of  $\text{B}_2\text{O}_3$  were  
 5 contained in a crucible made of PBN and having an inner diameter of 150 mm. The interior of  
 the LEC growth device was pressurized to 65 kg/cm<sup>2</sup> (gauge pressure) and the crucible was  
 heated to 1400°C to form the GaAs melt. The pressure was then reduced to 20 kg/cm<sup>2</sup>. While  
 the crucible and a seed crystal were rotated at 10 rpm in an anticlockwise direction and 8 rpm  
 in a clockwise direction, respectively, the seed crystal was brought into contact with the GaAs  
 10 melt and then pulled upwards at a speed of 7 mm/h to attain a growth of a GaAs single crystal  
 in the <100> direction. The obtained GaAs single crystal had a weight of 2000 g and a  
 diameter of 80 mm.

A {100} wafer was cut from the top end of a straight body portion of the single crystal where  
 the fraction solidified was 0.10. The fraction solidified indicates a weight ratio of the ingot  
 15 portion at a side adjacent to the seed crystal and above the wafer relative to the whole ingot.  
 The wafer was subjected to measurement of the EPD and resistivity. Epd was uniform through-  
 out the wafer, including its peripheral portion, and was 1500 cm<sup>-2</sup>. Neither lineage (linear defects)  
 nor defects by precipitates were detected throughout the wafer. The resistivity exhibited a  
 tendency to decrease at an outer peripheral portion of the wafer, but was  $1 \times 10^7 \Omega\text{-cm}$  or  
 20 higher throughout the major portion of the wafer.

Another {100} wafer was cut from a straight body portion of the single crystal where the  
 fraction solidified was 0.61 and subjected to the EPD measurement. The EPD was slightly high,  
 but the average EPD taken from eight points across the diameter of the wafer was 2400 cm<sup>-2</sup>,  
 and the highest EPD was 2850 cm<sup>-2</sup>.

### Comparative Example 2

The same crystal growth procedure of Example 3 was repeated except that  $\text{Ga}_2\text{O}_3$  and  $\text{As}_2\text{O}_3$   
 was not added.

A wafer was cut from an upper straight body portion of the ingot where the fraction solidified  
 30 was 0.12 and subjected to the EPD measurement. The average EPD taken from nine points  
 across the diameter of the wafer was 10500 cm<sup>-2</sup>, and the minimum and highest EPDs were  
 6000 cm<sup>-2</sup> and 25000 cm<sup>-2</sup>, respectively.

### CLAIMS

35 1. A single crystal of IIIb-Vb group compound having a low dislocation density, characterized  
 by containing from  $1 \times 10^{17}$  to  $8 \times 10^{19} \text{ cm}^{-3}$  of oxygen.

2. A single crystal of IIIb-Vb group compound according to claim 1, which consists of gallium  
 arsenide.

40 3. A single crystal of gallium arsenide according to claim 2, which contains from  $1 \times 10^{18}$  to  
 $1 \times 10^{20} \text{ cm}^{-3}$  of indium.

4. A single crystal of IIIb-Vb group compound according to claim 1, 2, or 3, wherein said  
 single crystal is produced by single crystal growth from a melt of said IIIb-Vb group compound,  
 which contains from  $1 \times 10^{18}$  to  $2 \times 10^{21} \text{ cm}^{-3}$  of oxygen atom.

45 5. A single crystal of IIIb-Vb group compound according to claim 4, wherein said single  
 crystal is grown by liquid encapsulated Czochralsky method.

6. A method for producing a single crystal of a IIIb-Vb group compound from a melt of the  
 IIIb-Vb group compound by a liquid encapsulated Czochralsky method, characterized in that at  
 least one oxide selected from the group consisting of an oxide of said IIIb group-element and an  
 oxide of said Vb group-element is added to said melt at an amount of from  $1 \times 10^{17}$  to  $2 \times 10^{21}$   
 50 of oxygen atoms of said oxide(s) per cm<sup>3</sup> of said melt.

7. A method according to claim 6, wherein said IIIb-Vb group element GaAs and said group  
 consists of gallium oxide and diarsenic trioxide.

8. A method according to claim 7, wherein gallium oxide and diarsenic trioxide are added at  
 equal molar amounts.

55 9. A method according to claim 6, 7, or 8, wherein indium oxide is added to said melt.